

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete If Known	
		Application Number	10/790,420
		Filing Date	Concurrently Herewith
		First Named Inventor	Jian Chen
		Group Art Unit	2818
Examiner Name		Attorney Docket Number	SC13210TP

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. 1	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
He	AA	5,461,243	10/24/1995	Ek <i>et al.</i>	
	AB	5,759,898	06/02/1998	Ek <i>et al.</i>	
	AC	5,846,857	12/08/1998	Ju	
	AD	5,943,565	08/24/1999	Ju	
	AE	6,369,438 B1	04/09/2002	Sugiyama <i>et al.</i>	
	AF	2003/0034529 A1	10/08/2002	Fitzgerald	
	AG	2003/0013305 A1	01/16/2003	Sugii <i>et al.</i>	
	AH	6,524,935 B1	02/25/2003	Canaperi <i>et al.</i>	
He	AI	2003/0040160 A1	02/27/2003	Huang <i>et al.</i>	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ Number ⁴ Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
THP	AJ	JP 2000243946	12/06/1999	Naoharu <i>et al.</i>		Yes/Abstract
THP	AK	WO 02/33746 A1	04/22/2002	Chu <i>et al.</i>		

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
THP	AL	Chi <i>et al.</i> , "Electrically active defects in surface preamorphized and subsequently RTP-annealed Si and the effect of titanium silicidation," <i>Proc. 1998 5th International Conference on Solid-State and Integrated Circuit Technology</i> , October 21, 1998, Beijing, China, p. 324-327.	
	AM	Fahey <i>et al.</i> , "Point defects and dopant diffusion in silicon," <i>Reviews of Modern Physics</i> , April 1989, Vol. 61, No. 2, pp. 289-384.	
	AN	Lee <i>et al.</i> , "Sub-30 nm P+ abrupt junction formation in Strained Si/Si _{1-x} Ge _x MOS device," <i>Technical Digest of the International Electron Devices Meeting</i> , December 8, 2002, pp. 379-81.	
	AO	LeGoues <i>et al.</i> , "Kinetics and Mechanism of Oxidation of SiGe: Dry Versus Wet Oxidation," <i>Applied Physics Letters</i> , February 13, 1989, Vol. 54, No. 7, pp. 644-646.	
	AP	LeGoues <i>et al.</i> , "Oxidation Studies of SiGe," <i>Journal of Applied Physics</i> , February 15, 1989, Vol. 65, No. 4, pp. 1724-1728.	
	AQ	Lim <i>et al.</i> , "Dry Thermal Oxidation of a Graded SiGe Layer," <i>Applied Physics Letters</i> , November 26, 2001, Vol. 79, No. 22, pp. 3606-3608.	
	AR	Sawano <i>et al.</i> , "Relaxation Enhancement of SiGe Thin Layers by Ion Implantation into Si Substrates," <i>IEEE</i> , 2002, pp. 403-404.	
	AS	Tezuka <i>et al.</i> , "Dislocation-free Formation of Relaxed SiGe-on-insulator Layers," <i>Applied Physics Letters</i> , May 13, 2002, Vol. 80, No. 19, pp. 3560-3562.	
	AT	Tezuka <i>et al.</i> , "Fabrication of Strained Si on an Ultrathin SiGe-on-insulator Virtual Substrate with a High-Ge Fraction," <i>Applied Physics Letters</i> , September 17, 2001, Vol. 79, No. 12, pp. 1798-1800.	
	AU	Vyatkin <i>et al.</i> , "Ion Beam Induced Strain Relaxation in Pseudomorphous Epitaxial SiGe Layers," <i>IEEE</i> , 2000, pp. 70-72.	
THP	AV	U.S. Patent Application S/N 10/670,928 filed 09/25/2003, entitled "SOI Template Layer", same assignee as assignee hereof.	

Examiner Signature	THP - THP HIO	Date Considered	June 2005
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¹ Unique citation designation number. ² See Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English Language Translation is attached.

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